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Sheet 1 of 1

FORM PTO-1449 (SUBSTITUTE)				Attorney Docket No.: GR 98 P 5874 P		Applic. No. 09/873,227	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				Applicant Daniel Reznik			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Filing Date June 4, 2001		Group Art Unit 2822	
U.S. PATENT DOCUMENTS							
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	5,608,237	03/04/97	Aizawa et al			
	B	5,766,966	06/16/98	Ng			
	C						
	D						
	E						
	F						
	G						
	H						
	I						
FOREIGN PATENT DOCUMENT							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J	0 837 508 A2	04/22/98	Europe			X
	K	WO 98/38681	09/03/98	WIPO			X
	L						
	M						
	N						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
	O	M. Mori et al.: "A Novel High-Conductivity IGBT (HiGT) with a Short Circuit Capability", <i>Proceedings of 1998 International Symposium on Power Semiconductor Devices & ICs, Kyoto, Japan</i> , pp. 429-432, XP-000801108					
	P						
EXAMINER				DATE CONSIDERED 2/4/03			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							